

## General Description

The ICS840N0511 is a LVCMOS/LVTTL clock synthesizer designed for SDH/SONET and Ethernet applications. The device generates a selectable 155.52MHz or 77.76MHz clock signal with excellent phase jitter performance. The device uses IDT's fourth generation FemtoClock® NG technology for an optimum of high clock frequency, low phase noise performance and low power consumption. The device supports 2.5V or 3.3V voltage supply and is packaged in a small, lead-free (RoHS 6) 8-lead TSSOP package. The extended temperature range supports wireless infrastructure, telecommunication and networking end equipment requirements.

## Features

- Fourth generation FemtoClock® NG technology
- 155.52MHz output clock synthesized from a 19.44MHz fundamental mode crystal
- One 2.5V or 3.3V LVCMOS/LVTTL clock output
- Crystal interface designed for a 12pF parallel resonant crystal
- RMS phase jitter @ 155.52MHz, using a 19.44MHz crystal (12kHz - 20MHz): 0.482ps (maximum)
- RMS phase jitter @ 156.25MHz, using a 19.53125MHz crystal (1.875MHz - 20MHz): 0.138ps (maximum)
- LVCMOS interface levels for the control inputs
- Full 2.5V or 3.3V supply voltage
- Lead-free (RoHS 6) packaging
- -40°C to 85°C ambient operating temperature

### OE Function Table

| Input       | Output Enable                                |
|-------------|--|
| OE          |  |
| 0           | Output Q is disabled in high-impedance state |
| 1 (default) | Output Q is enabled.                         |

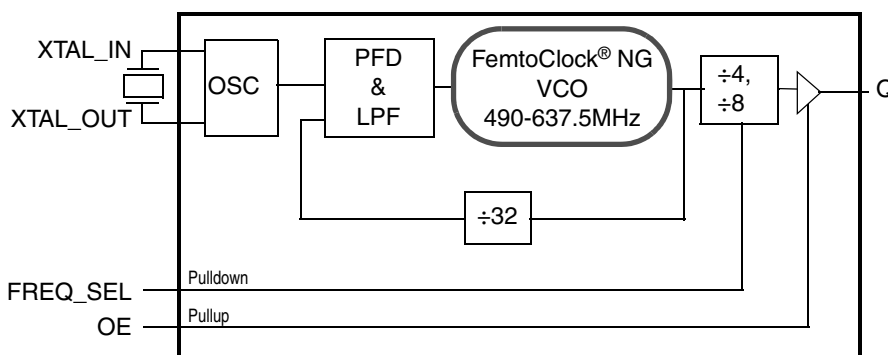
NOTE: OE is an asynchronous control

### FREQ\_SEL Frequency Table

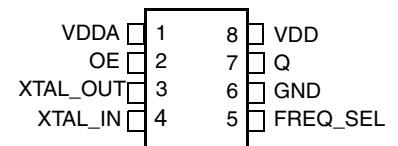
| Input       | Output Frequency            |                              |                                 |
|-------------|-----------------------------|------------------------------|---------------------------------|
|             | f <sub>XTAL</sub> = 19.2MHz | f <sub>XTAL</sub> = 19.44MHz | f <sub>XTAL</sub> = 19.53125MHz |
| 0 (default) | 153.6MHz                    | 155.52MHz                    | 156.25MHz                       |
| 1           | 76.8MHz                     | 77.76MHz                     | 78.125MHz                       |

NOTE: FREQ\_SEL is an asynchronous control.

## Block Diagram



## Pin Assignment



**ICS840N0511**  
**8-lead TSSOP**  
**4.40mm x 3.0mm x 0.925mm**  
**package body**  
**G Package**  
**Top View**

## Pin Descriptions and Characteristics

**Table 1. Pin Descriptions**

| Number  | Name                 | Type   |          | Description   |
|---------|----------------------|--------|----------|---|
| 1       | V <sub>DDA</sub>     | Power  |          | Analog power supply.  |
| 2       | OE                   | Input  | Pullup   | Output enable pin. LVCMOS interface levels.                                 |
| 3,<br>4 | XTAL_OUT,<br>XTAL_IN | Input  |          | Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output. |
| 5       | FREQ_SEL             | Input  | Pulldown | Frequency select pin. LVCMOS interface levels.                              |
| 6       | GND                  | Power  |          | Power supply ground.  |
| 7       | Q                    | Output |          | Single-ended clock output. LVCMOS/LVTTL interface levels.                   |
| 8       | V <sub>DD</sub>      | Power  |          | Core supply pin.  |

NOTE: *Pulldown* and *Pullup* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

| Symbol                | Parameter                     | Test Conditions          | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------------|--------------------------|---------|---------|---------|-------|
| C <sub>IN</sub>       | Input Capacitance             | OE, FREQ_SEL             |         | 3.5     |         | pF    |
| C <sub>PD</sub>       | Power Dissipation Capacitance | V <sub>DD</sub> = 3.465V |         | 11      |         | pF    |
|                       |                               | V <sub>DD</sub> = 2.625V |         | 9       |         | pF    |
| R <sub>Pullup</sub>   | Input Pullup Resistor         |                          |         | 51      |         | kΩ    |
| R <sub>Pulldown</sub> | Input Pulldown Resistor       |                          |         | 51      |         | kΩ    |
| R <sub>OUT</sub>      | Output Impedance              | V <sub>DD</sub> = 3.3V   |         | 15      |         | Ω     |
|                       |                               | V <sub>DD</sub> = 2.5V   |         | 19      |         | Ω     |

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item                                     | Rating                               |
|--|--------------------------------------|
| Supply Voltage, $V_{DD}$                 | 3.63V                                |
| Inputs, $V_I$<br>XTAL_IN<br>Other Inputs | 0V to 2V<br>-0.5V to $V_{DD} + 0.5V$ |
| Outputs, $V_O$                           | -0.5V to $V_{DD} + 0.5V$             |
| Package Thermal Impedance, $\theta_{JA}$ | 117°C/W (0 mps)                      |
| Storage Temperature, $T_{STG}$           | -65°C to 150°C                       |

## DC Electrical Characteristics

**Table 3A. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

| Symbol    | Parameter             | Test Conditions | Minimum         | Typical | Maximum  | Units |
|-----------|-----------------------|-----------------|-----------------|---------|----------|-------|
| $V_{DD}$  | Core Supply Voltage   |                 | 2.375           | 3.3     | 3.465    | V     |
| $V_{DDA}$ | Analog Supply Voltage |                 | $V_{DD} - 0.18$ | 3.3     | $V_{DD}$ | V     |
| $V_{DDA}$ | Analog Supply Voltage |                 | $V_{DD} - 0.18$ | 2.5     | $V_{DD}$ | V     |
| $I_{DDA}$ | Analog Supply Current |                 |                 |         | 18       | mA    |
| $I_{DD}$  | Power Supply Current  |                 |                 |         | 67       | mA    |

**Table 3B. LVCMOS/LVTTL DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

| Symbol   | Parameter                      | Test Conditions   | Minimum | Typical | Maximum        | Units         |
|----------|--------------------------------|---|---------|---------|----------------|---------------|
| $V_{IH}$ | Input High Voltage             | $V_{DD} = 3.3V$   | 2       |         | $V_{DD} + 0.3$ | V             |
|          |                                | $V_{DD} = 2.5V$   | 1.7     |         | $V_{DD} + 0.3$ | V             |
| $V_{IL}$ | Input Low Voltage              | FREQ_SEL<br>$V_{DD} = 3.3V$                               | -0.3    |         | 0.5            | V             |
|          |                                | OE<br>$V_{DD} = 3.3V$                                     | -0.3    |         | 0.8            | V             |
|          |                                | FREQ_SEL<br>$V_{DD} = 2.5V$                               | -0.3    |         | 0.5            | V             |
|          |                                | OE<br>$V_{DD} = 2.5V$                                     | -0.3    |         | 0.7            | V             |
| $I_{IH}$ | Input High Current             | FREQ_SEL<br>$V_{DD} = V_{IN} = 3.465V$ or $2.625V$        |         |         | 150            | $\mu\text{A}$ |
|          |                                | OE<br>$V_{DD} = V_{IN} = 3.465V$ or $2.625V$              |         |         | 5              | $\mu\text{A}$ |
| $I_{IL}$ | Input Low Current              | FREQ_SEL<br>$V_{DD} = 3.465V$ or $2.625V$ , $V_{IN} = 0V$ | -5      |         |                | $\mu\text{A}$ |
|          |                                | OE<br>$V_{DD} = 3.465V$ or $2.625V$ , $V_{IN} = 0V$       | -150    |         |                | $\mu\text{A}$ |
| $V_{OH}$ | Output High Voltage;<br>NOTE 1 | Q<br>$V_{DD} = 3.465V$                                    | 2.6     |         |                | V             |
|          |                                | Q<br>$V_{DD} = 2.625V$                                    | 1.8     |         |                | V             |
| $V_{OL}$ | Output Low Voltage;<br>NOTE 1  | Q<br>$V_{DD} = 3.465V$ or $2.625V$                        |         |         | 0.5            | V             |

NOTE 1: Output terminated with  $50\Omega$  to  $V_{DD} / 2$ . See Parameter Measurement Information Section, *LVCMOS Output Load Test Circuit Diagrams*.

**Table 4. Crystal Characteristics**

| Parameter                          | Test Conditions | Minimum     | Typical | Maximum | Units    |
|------------------------------------|-----------------|-------------|---------|---------|----------|
| Mode of Oscillation                |                 | Fundamental |         |         |          |
| Frequency                          |                 | 15.31       | 19.44   | 19.92   | MHz      |
| Equivalent Series Resistance (ESR) |                 |             |         | 80      | $\Omega$ |
| Shunt Capacitance                  |                 |             |         | 7       | pF       |
| Capacitive Load (CL)               |                 |             | 12      |         | pF       |

## AC Characteristics

**Table 5. AC Characteristics,  $V_{DD} = V_{DDA} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$** 

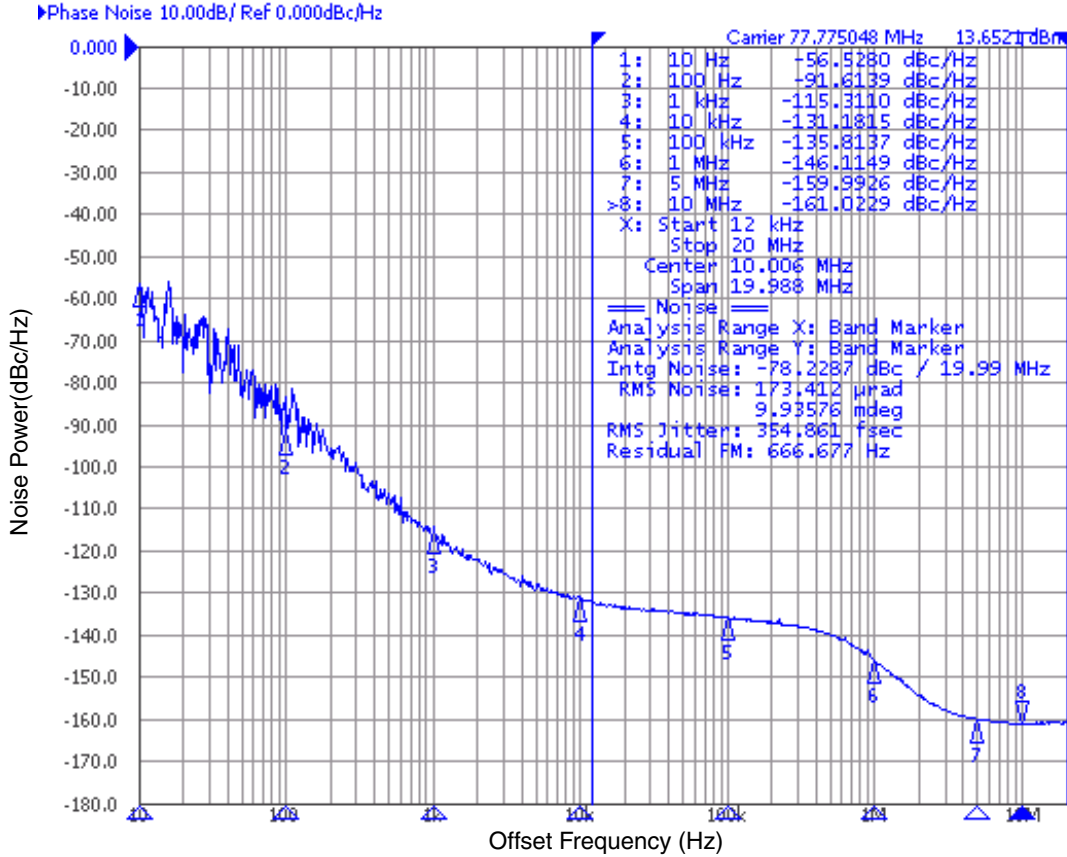
| Symbol               | Parameter                         | Test Conditions  | Minimum | Typical | Maximum | Units  |
|----------------------|-----------------------------------|--|---------|---------|---------|--------|
| $f_{OUT}$            | Output Frequency                  | FREQ_SEL = 0   | 122.5   | 155.52  | 159.38  | MHz    |
|                      |                                   | FREQ_SEL = 1   | 61.25   | 77.76   | 79.69   | MHz    |
| $f_{jit}(\emptyset)$ | RMS Phase Jitter (Random); NOTE 1 | $f_{OUT} = 155.52\text{MHz}$ , Integration Range: 12kHz – 20MHz, 19.44MHz crystal        |         | 0.350   | 0.482   | ps     |
|                      |                                   | $f_{OUT} = 77.76\text{MHz}$ , Integration Range: 12kHz – 20MHz, 19.44MHz crystal         |         | 0.354   | 0.508   | ps     |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Integration Range: 1.875MHz – 20MHz, 19.353125MHz crystal |         | 0.101   | 0.138   | ps     |
| $\Phi_N$             | Single-Side Band Noise Power      | $f_{OUT} = 156.25\text{MHz}$ , Offset: 10Hz  |         | -43.6   |         | dBc/Hz |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Offset: 100Hz   |         | -74.1   |         | dBc/Hz |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Offset: 1kHz  |         | -107.3  |         | dBc/Hz |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Offset: 10kHz   |         | -124.4  |         | dBc/Hz |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Offset: 100kHz  |         | -128.9  |         | dBc/Hz |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Offset: 1MHz  |         | -139.1  |         | dBc/Hz |
|                      |                                   | $f_{OUT} = 156.25\text{MHz}$ , Offset: 10MHz   |         | -156.7  |         | dBc/Hz |
| $t_R / t_F$          | Output Rise/Fall Time             | 20% to 80%   | 200     |         | 600     | ps     |
| odc                  | Output Duty Cycle                 |  | 48      |         | 52      | %      |

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

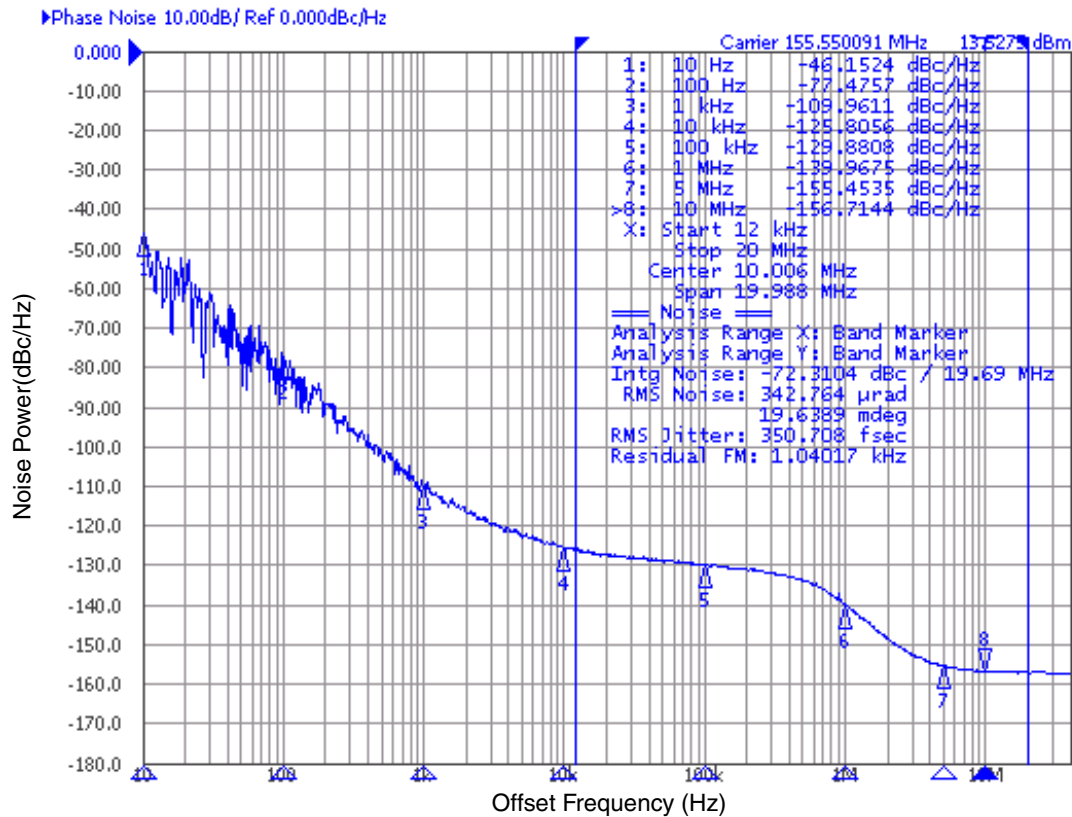
NOTE: Characterized with 19.2MHz, 19.44MHz and 19.53125MHz crystals.

NOTE 1: Please refer to the phase noise plots.

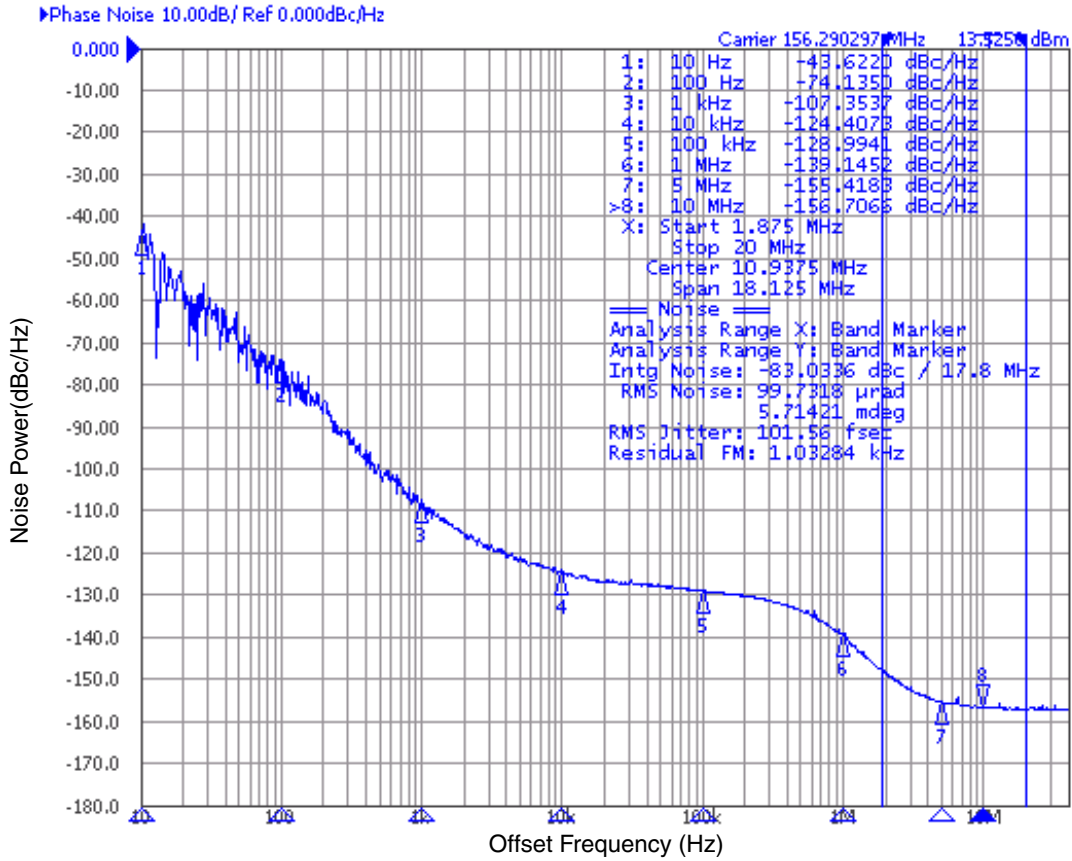
## Typical Phase Noise at 77.76MHz



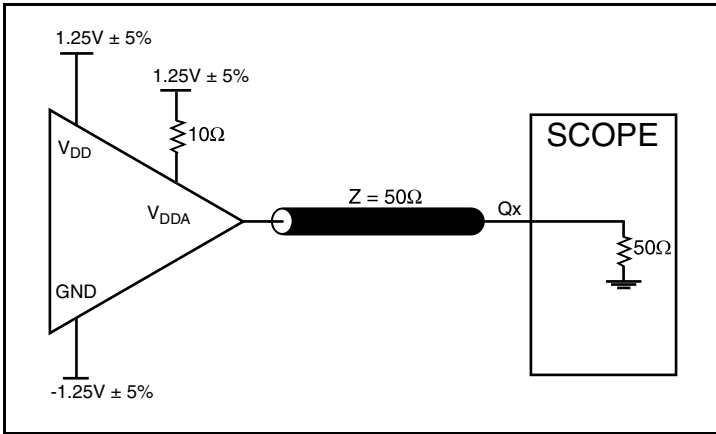
## Typical Phase Noise at 155.52MHz



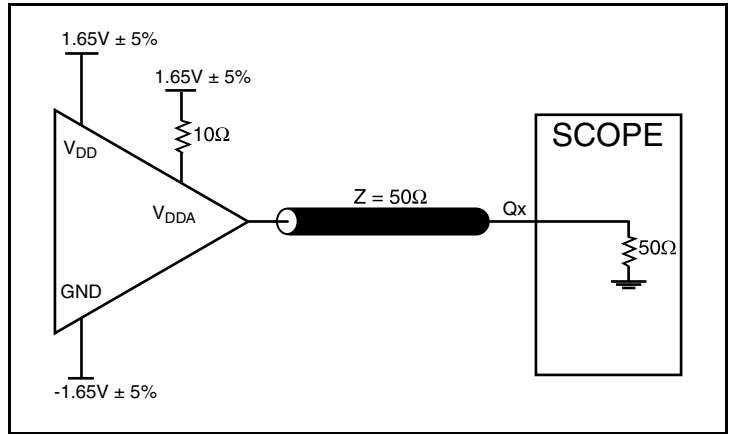
## Typical Phase Noise at 156.25MHz



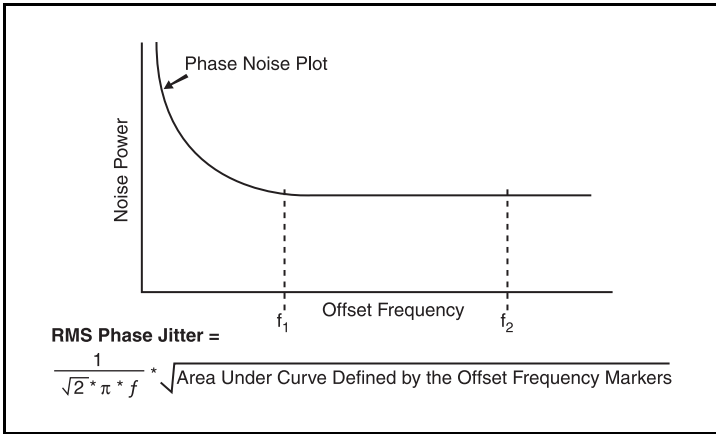
## Parameter Measurement Information



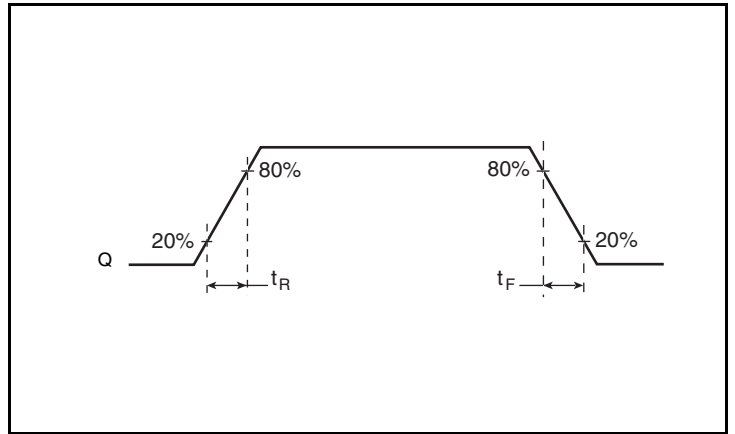
2.5V LVCMOS/LVTTL Output Load AC Test Circuit



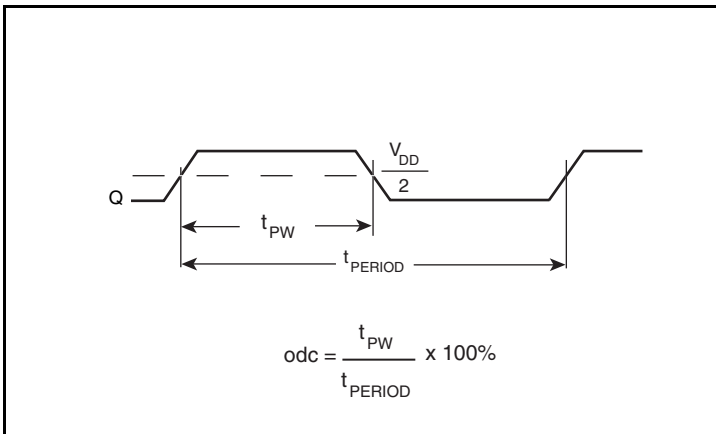
3.3V LVCMOS/LVTTL Output Load AC Test Circuit



RMS Phase Jitter



Output Rise/Fall Time



Output Duty Cycle/Pulse Width/Period

## Applications Information

### Overdriving the XTAL Interface

The XTAL\_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL\_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 1A* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver ( $R_o$ ) and the series resistance ( $R_s$ ) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This

can be done in one of two ways. First,  $R_1$  and  $R_2$  in parallel should equal the transmission line impedance. For most 50Ω applications,  $R_1$  and  $R_2$  can be 100Ω. This can also be accomplished by removing  $R_1$  and changing  $R_2$  to 50Ω. The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. *Figure 1B* shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL\_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

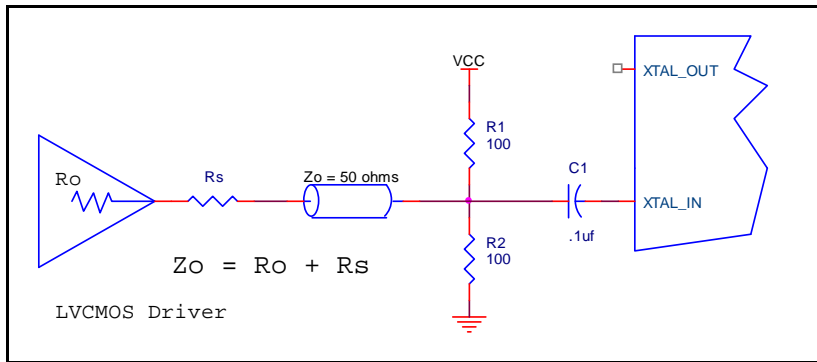


Figure 1A. General Diagram for LVCMOS Driver to XTAL Input Interface

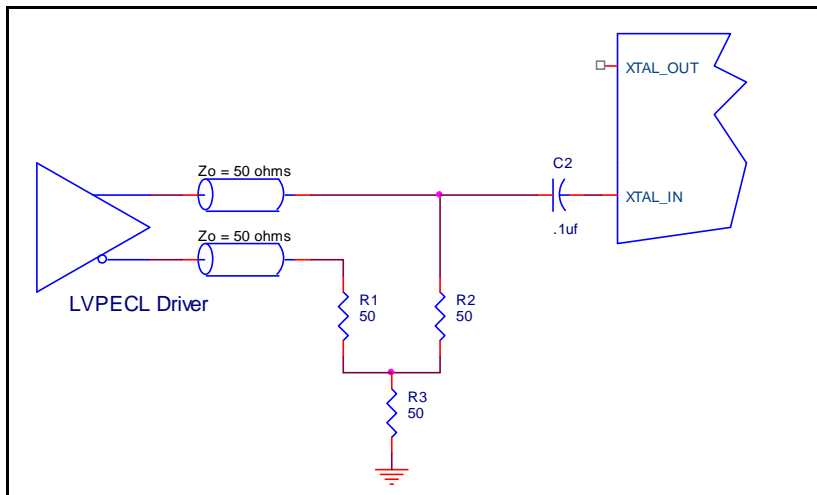


Figure 1B. General Diagram for LVPECL Driver to XTAL Input Interface



## Schematic Layout

Figure 2 shows an example ICS840N051I application schematic in which the device is operated at  $V_{DD} = V_{DDA} = 3.3V$ . The schematic example focuses on functional connections and is intended as an example only and may not represent the exact user configuration. Refer to the pin description and functional tables in the datasheet to ensure the logic control inputs are properly set. For example OE and FREQ\_SEL can be configured from an FPGA instead of set with pull up and pull down resistors as shown.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise, so to achieve optimum jitter performance isolation of the  $V_{DD}$  pin from power supply is required. In order to achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB

as close to the power pins as possible. If space is limited, the  $0.1\mu F$  capacitor on the  $V_{DD}$  pin must be placed on the device side with direct return to the ground plane though vias. The remaining filter components can be on the opposite side of the PCB.

Power supply filter recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10kHz. If a specific frequency noise component is known, such as switching power supply frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally, good general design practices for power plane voltage stability suggests adding bulk capacitances in the local area of all devices.

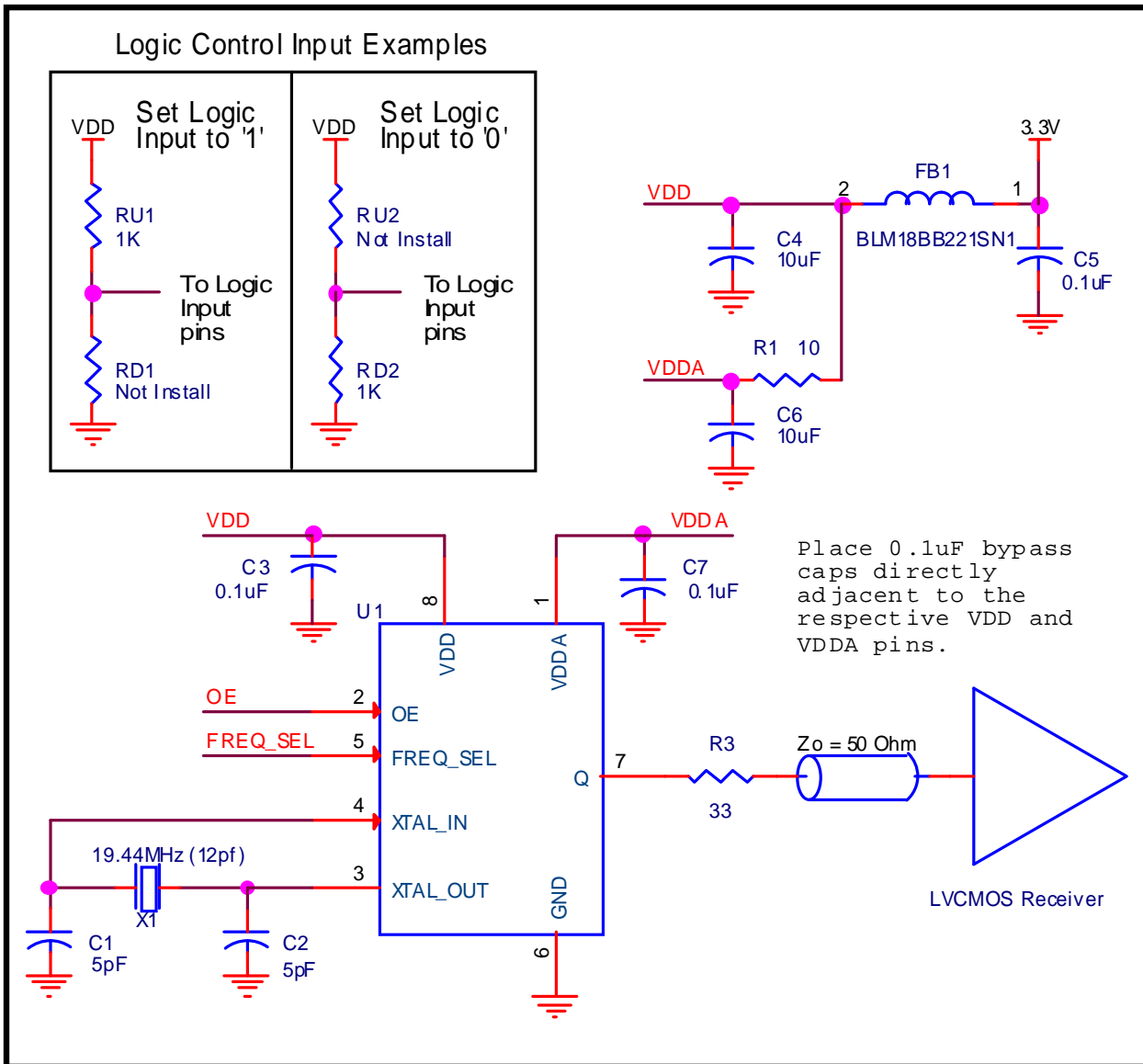


Figure 2. ICS840N051I Application Schematic

## Power Considerations

This section provides information on power dissipation and junction temperature for the ICS840N051I. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the ICS840N051I is the sum of the core power plus the analog power plus the power dissipated into the load. The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

- Power (core)<sub>MAX</sub> =  $V_{DD\_MAX} * (I_{DD} + I_{DDA}) = 3.465V * (67mA + 18mA) = \mathbf{294.53mW}$
- Output Impedance  $R_{OUT}$  Current due to Loading  $50\Omega$  to  $V_{DD}/2$   
Output Current  $I_{OUT} = V_{DD\_MAX} / [2 * (50\Omega + R_{OUT})] = 3.465V / [2 * (50\Omega + 15\Omega)] = \mathbf{26.7mA}$
- Power Dissipation on the  $R_{OUT}$  per LVCMOS output  
Power ( $R_{OUT}$ ) =  $R_{OUT} * (I_{OUT})^2 = 15\Omega * (26.7mA)^2 = \mathbf{10.7mW}$  per output
- Total Power ( $R_{OUT}$ ) =  $10.7mW * 1 = \mathbf{10.7mW}$

### Dynamic Power Dissipation at 156.25MHz

$$\text{Power (156.25MHz)} = C_{PD} * \text{Frequency} * (V_{DD})^2 = 11pF * 156.25MHz * (3.465V)^2 = \mathbf{20.64mW}$$

$$\text{Total Power (156.25MHz)} = 20.64mW * 1 = \mathbf{20.64mW}$$

### Total Power Dissipation

- **Total Power**  
= Power (core)<sub>MAX</sub> + Power ( $R_{OUT}$ ) + Power (156.25MHz)  
=  $294.53mW + 10.7mW + 20.64mW$   
=  $\mathbf{325.87mW}$

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature,  $T_j$ , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd\_total + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd\_total$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 117°C/W per Table 6 below.

Therefore,  $T_j$  for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.326W * 117^\circ\text{C/W} = 123.2^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

**Table 6. Thermal Resistance  $\theta_{JA}$  for 8 Lead TSSOP, Forced Convection**

| $\theta_{JA}$ by Velocity                   |          |
|---|----------|
| Meters per Second                           | <b>0</b> |
| Multi-Layer PCB, JEDEC Standard Test Boards | 117°C/W  |



## Ordering Information

Table 9. Ordering Information

| Part/Order Number | Marking | Package                 | Shipping Packaging | Temperature   |
|-------------------|---------|-------------------------|--------------------|---------------|
| 840N051BGILF      | 51BIL   | Lead-Free, 8-lead TSSOP | Tube               | -40°C to 85°C |
| 840N051BGILFT     | 51BIL   | Lead-Free, 8-lead TSSOP | Tape & Reel        | -40°C to 85°C |

## Revision History Sheet

| Rev | Table | Page | Description of Change  | Date       |
|-----|-------|------|--|------------|
| A   |       | 1    | General Description - corrected output frequency of 156.25MHz to 155.52MHz in second sentence. | 10/14/2013 |
|     |       |      |  |            |



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